

## TO-92 Plastic-Encapsulate Transistors

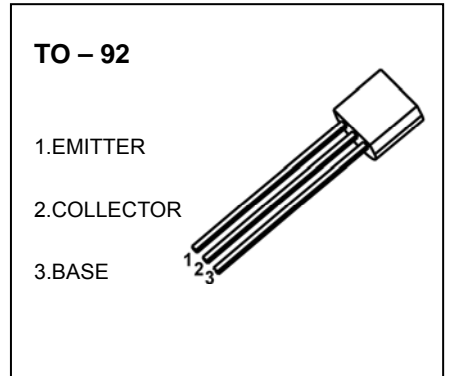
### 8550SS TRANSISTOR (PNP)

#### FEATURES

- General Purpose Switching and Amplification.

#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V
V <sub>EB0</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-1.5	A
P <sub>C</sub>	Collector Power Dissipation	1	W
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	125	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C



#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CB0</sub>	I <sub>C</sub> = -0.1mA, I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-0.1mA, I <sub>B</sub> =0	-25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-0.1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0			-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-20V, I <sub>B</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1, I <sub>C</sub> =-100mA	85		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-800mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA			-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA, f=30MHz	100			MHz

#### CLASSIFICATION OF h<sub>FE(1)</sub>

RANK	B	C	D
RANGE	85-160	120-200	160-300

# Typical Characteristics

# 8550SS

